Abstract of the Disclosure

A method of processing a wafer having devices in a plurality of areas sectioned by streets arranged in a lattice pattern on the front surface to form a metal film on a back surface thereof, wherein

a laser beam application step for applying a laser beam capable of passing through a wafer, along the streets formed on the wafer to form a deteriorated layer is carried out before a metal film forming step for forming a metal film on the back surface of the wafer.